

General Description

It combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

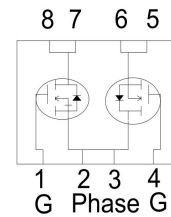
Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Half-Bridge - N-channel

Application

- BLDC Motor driver
- DC-DC

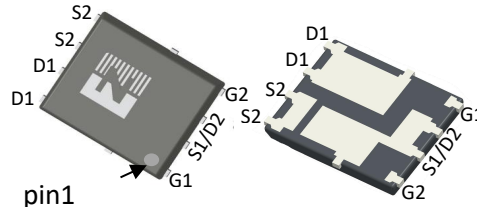
Product Summary



$$V_{DS} = 40V$$

$$R_{DS(ON)} = 5.5m\Omega$$

$$I_D = 54A$$



DFN5*6



Ordering Information:

Part NO.	ZMDA68412NB
Marking	ZMD68412
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	54	A
	I_D	$T_C=75^\circ C$	44	A
	I_D	$T_C=100^\circ C$	38	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^\circ C$;	216	A
Total Power Dissipation	P_D	$T_C=25^\circ C$	38	W
Total Power Dissipation	P_D	$T_A=25^\circ C$	3.3	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ C$
Storage Temperature	T_{STG}		-55 to +175	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1mH$, $V_{GS}=10V$, $R_g=25\Omega$,	25	mJ
		$L=0.5mH$, $V_{GS}=10V$, $R_g=25\Omega$,	40	mJ
ESD Level (HBM)	CLASS 2			

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	4	°C/W
Thermal resistance, junction-ambient ^②	R_{thJA}		-	45	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.3	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=14A$		5.5	6.7	m Ω
		$V_{GS}=4.5V, I_D=10A$		10	13	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$		20		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=14A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	637	-	pF
Output capacitance	C_{oss}		-	168	-	
Reverse transfer capacitance	C_{rss}		-	13	-	
Gate Resistance	R_g	$f=1MHz$	-	1.6		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	12	-	nC
	$Q_g(4.5V)$		-	7	-	
Gate - Source charge	Q_{gs}		-	2.1	-	
Gate - Drain charge	Q_{gd}		-	3.8	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	7	-	ns
Turn-ON Rise time	t_r		-	5	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	16	-	ns
Turn-Off Fall time	t_f		-	4	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, dI_S/dt=100A/\mu s, I_S=20A$	-	32	-	ns
Reverse Recovery Charge	Q_{RR}		-	45	-	nC

Fig.1 Gate-Charge Characteristics

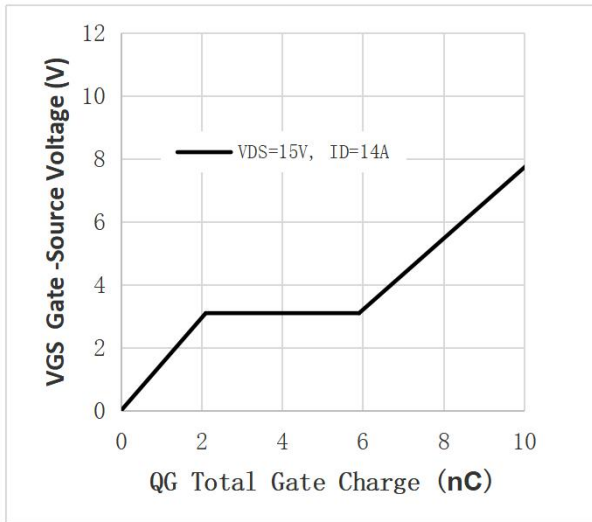


Fig.2 Capacitance Characteristics

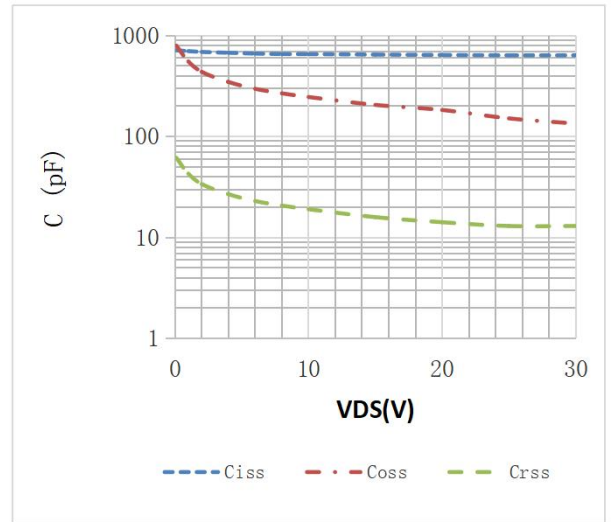


Fig.3 Power Dissipation

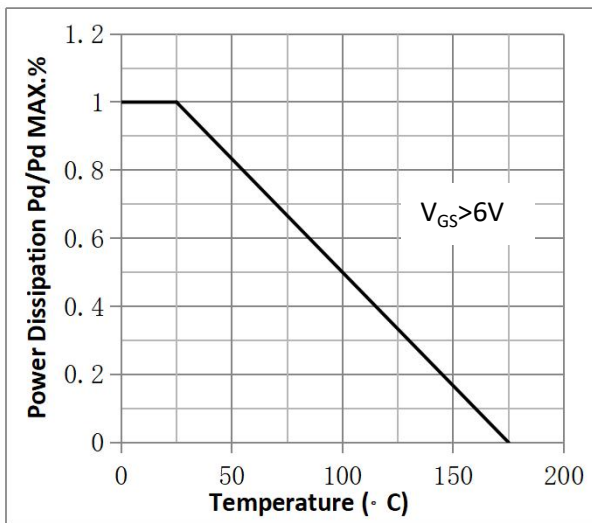


Fig.4 Typical output Characteristics

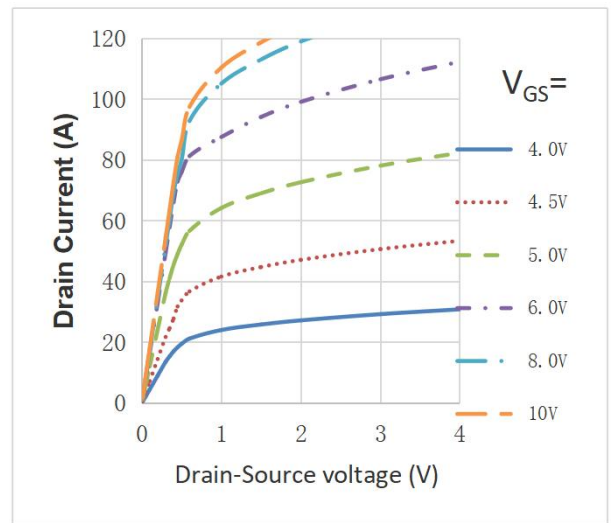


Fig.5 Threshold Voltage V.S Junction Temperature

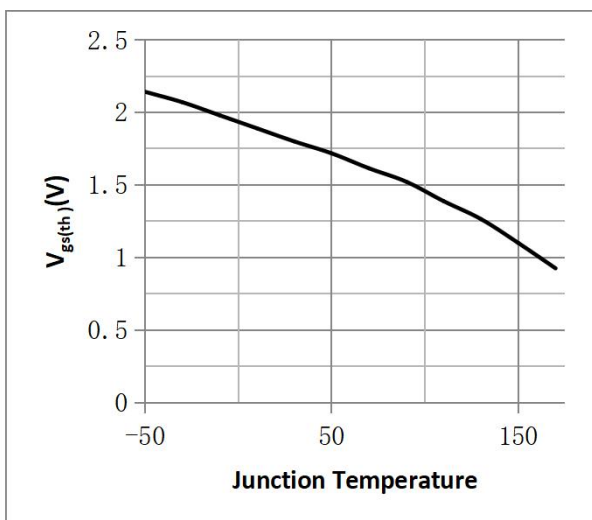


Fig.6 Resistance V.S Drain Current

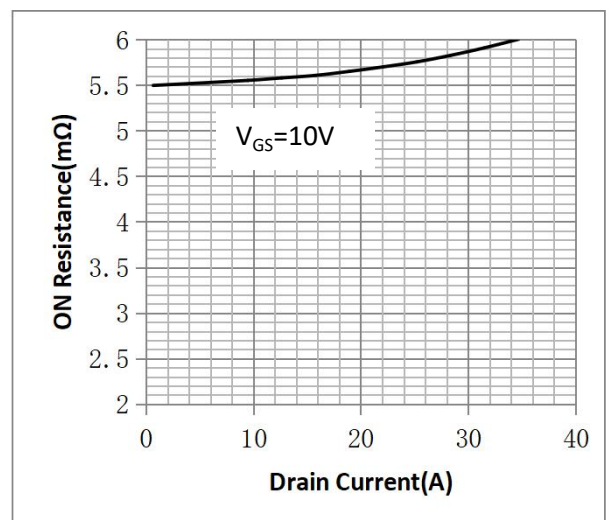


Fig.7 On-Resistance VS Gate Source Voltage

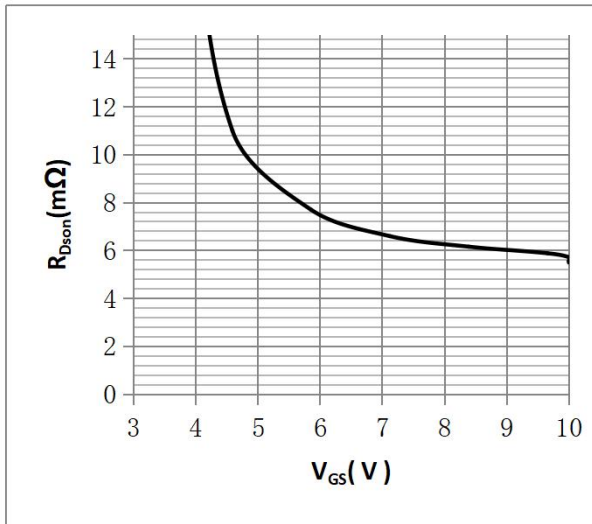


Fig.8 On-Resistance V.S Junction Temperature

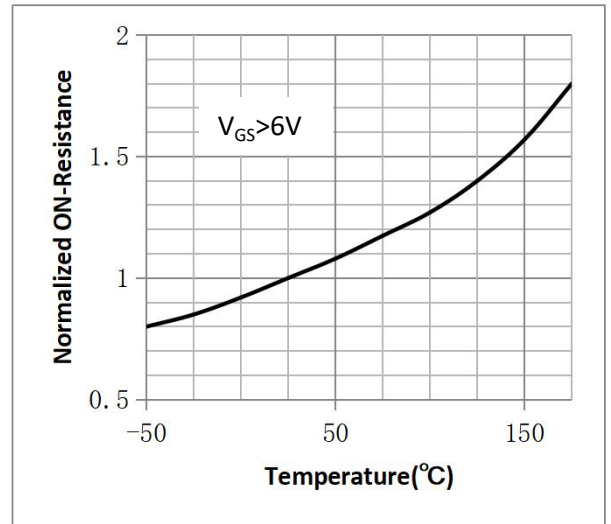


Figure 9. Diode Forward Voltage vs. Current

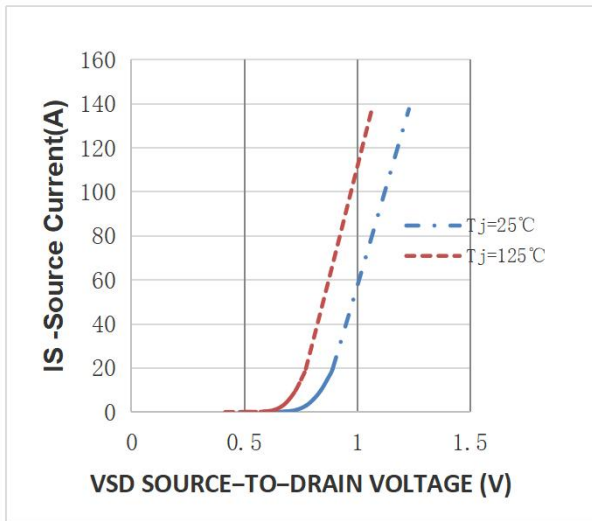


Figure 10. Transfer Characteristics

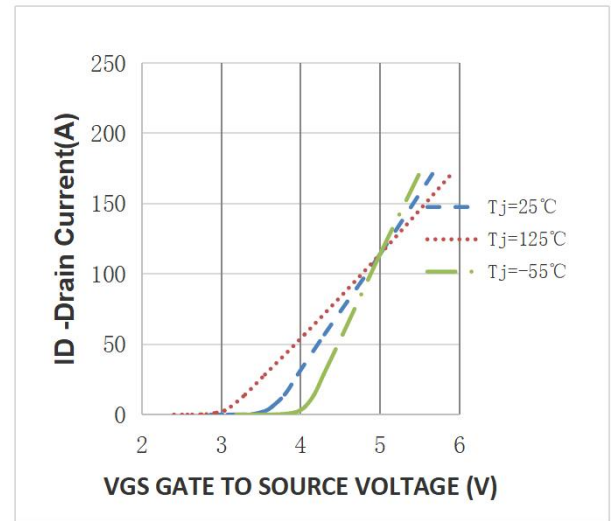


Fig.11 Safe Operating Area

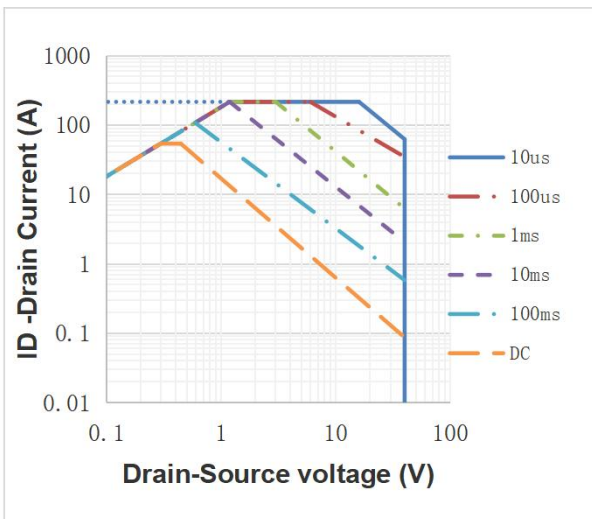
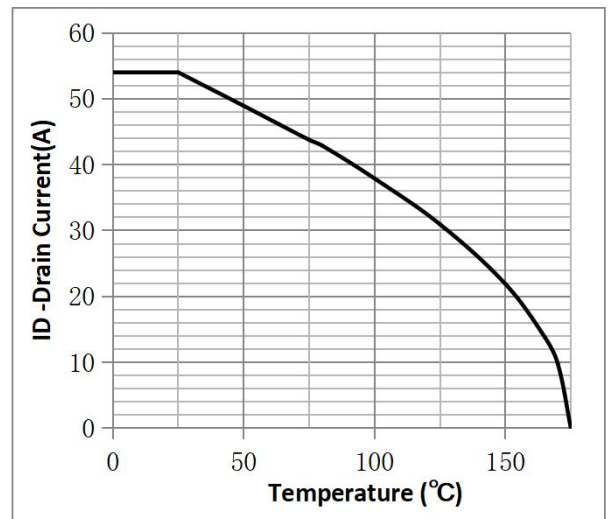
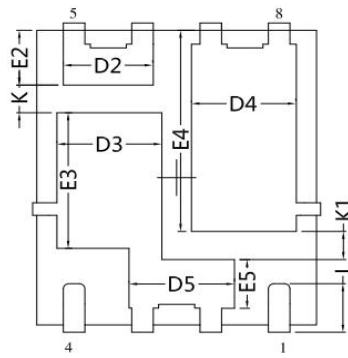
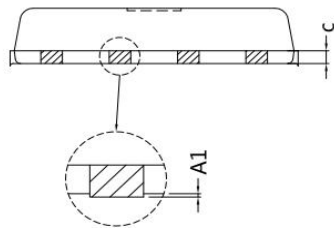
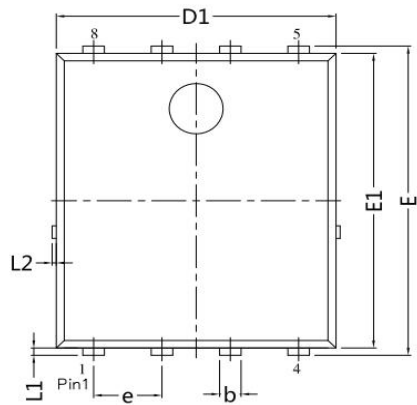


Fig.12 ID vs. Case Temperature^③



•DFN5*6 Package Outline



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.10	1.20
A1	0	---	0.05
b	0.30	0.40	0.50
c	0.20	0.25	0.30
D1	5.10	5.20	5.30
D2	1.52	1.67	1.82
D3	1.78	1.95	2.10
D4	1.78	1.95	2.10
D5	1.81	1.96	2.11
E	6.00	6.15	6.30
E1	5.76	5.86	5.96
E2	0.94	1.09	1.24
E3	2.55	2.70	2.85
E4	3.85	4.0	4.15
E5	0.82	0.97	1.12
e	1.27 BSC		
L	0.90	0.96	1.06
L1	0.05	0.15	0.25
L2	0.02	0.08	0.15
K	0.55	---	---
K1	0.56	---	---

Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2024.5.16	
B	2024.7.23	Correct PD,Rthjc
C	2024.9.12	Modified ciss, Qg